

CMUDW6001

**SURFACE MOUNT
ULTRA LOW LEAKAGE
SILICON SWITCHING DIODE**

ULTRAmi[™]



SOT-523W CASE



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMUDW6001 type is a silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a ULTRAmi[™] surface mount package, designed for switching applications requiring a extremely low leakage diode.

MARKING CODE: 61W

APPLICATIONS:

- Steering diode
- Flyback diode
- Voltage multiplier
- Reverse polarity protection

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$	I_{FSM}	4.0	A
Peak Forward Surge Current, $t_p=1.0\text{s}$	I_{FSM}	1.0	A
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	500	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

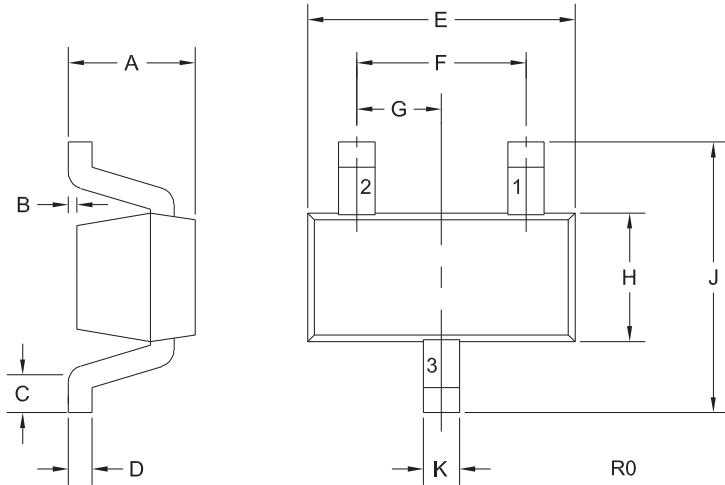
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=75\text{V}$		250	500	pA
BV_R	$I_R=100\mu\text{A}$	100	125		V
V_F	$I_F=1.0\text{mA}$		0.76	0.85	V
V_F	$I_F=10\text{mA}$		0.85	0.95	V
V_F	$I_F=100\text{mA}$		0.99	1.1	V
C_T	$V_R=0, f=1.0\text{MHz}$		1.7	2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			3.0	μs

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SOT-523W CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Anode
- 2) No Connection
- 3) Cathode

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SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	-	0.031	-	0.80
B	0.000	0.004	0.00	0.10
C	0.006	0.012	0.15	0.30
D	0.005	0.006	0.13	0.15
E	0.058	0.066	1.48	1.68
F	0.039		1.00	
G	0.020		0.50	
H	0.026	0.034	0.66	0.86
J	0.059	0.067	1.50	1.70
K	0.007	0.009	0.19	0.24

SOT-523W (REV: R0)

R3 (23-November 2011)

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